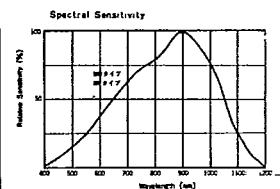


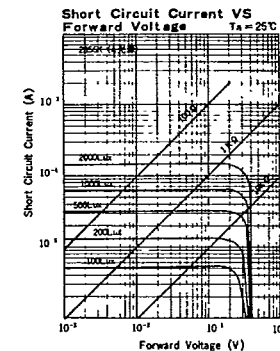
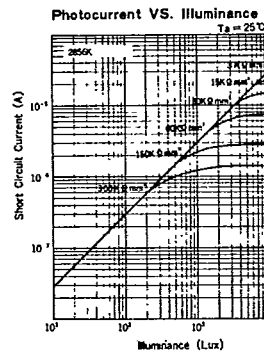
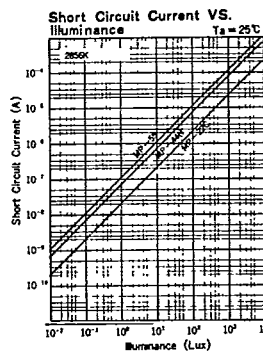
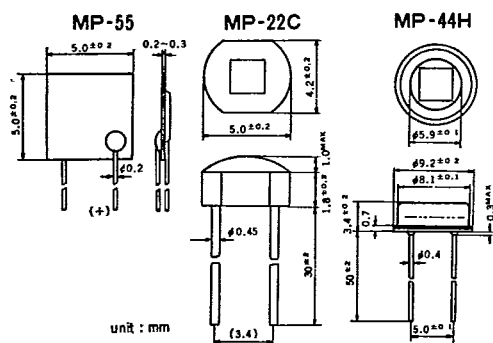
SILICON SENSORS INC

SILICON PLANAR PHOTODIODES**Maximum Ratings**

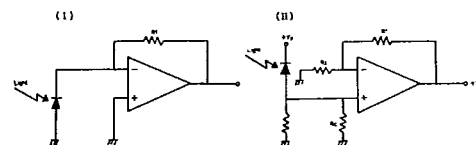
Ratings	Symbol	MP-55	MP-22C	MP-44H	Units
Reverse Voltage	V_R	30	30	30	V
Power Dissipation	P	0.3	0.05	0.2	mW
Operating Temperature	Topr.		- 0 ~ + 70		°C
Storage Temperature	Tstg		- 20 ~ + 80		°C

**Characteristics**

Ratings	Symbol	Conditions	MP-55 MIN. TYP. MAX.	MP-22C MIN. TYP. MAX.	MP-44H MIN. TYP. MAX.	Units
Short Circuit Current	I_{sc}	2856K 1000Lux	70 110	20 28	45 70	μA
Dark Current	I_d	$V_R = 1 V R_H < 65\%$	1 50	0.5 15	1 30	nA
Open Circuit Voltage	V_{oc}	2856 K 1000Lux	450	450	450	mV
Peak Sensitivity Wavelength	λ_p		900	900	900	nm
Response Time	tr, tf	1000Lux $R_S = 1 k\Omega$	8	2	5	μs
Temp. Coefficient of I_{sc}		2856 K 1000Lux	0.17	0.17	0.17	%/°C
Temp. Coefficient of V_{oc}		2856 K 1000Lux	- 3.0	- 3.3	- 3.0	mV/°C

**SILICON BLUE-SENSITIVE PHOTODIODES****Maximum Ratings** $T_a = 25^\circ C$

Ratings	Symbol	MBC-2014CF	MBC-3026CF	Units
Reverse Voltage	V_R	10	10	V
Operating Temperature	Topr.	- 20 ~ + 60		°C
Storage Temperature	Tstg	- 20 ~ + 80		°C

**Characteristics**

Ratings	Symbol	Conditions	MBC-2014CF MIN. TYP. MAX.	MBC-3026CF MIN. TYP. MAX.	Units
Short Circuit Current	I_{sc}	2856K 100Lux	120 170	400 550	nA
Dark Current	I_d	$V_R = 1 V R_H < 65\%$	1 10	3 10	pA
Open Circuit Voltage	V_{oc}	2856K 100Lux	140	140	mV
Peak Sensitivity Wavelength	λ_p		560 600	560 600	nm
Terminal Capacitance	C_t	$V_R = 1 V f = 1 MHz$	250 500	600 1400	pF
Temp. Coefficient of I_{sc}		2856K 100Lux	0.07	0.07	%/°C
Temp. Coefficient of I_d		$V_R = 1 V R_H \leq 65\%$	5	5	/10°C

